

EAST Search History

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|--|---|------------------|---------|---------------------|
| L1 | 668 | dummy adj capacitor | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/05/02 10:52 |
| L2 | 217 | L1 and dram | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/05/02 10:52 |
| L3 | 277 | sram and ferroelectric and @ad<"19971211" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L4 | 232 | (ferroelectric or high-k sbt pzt) near gate adj (insulator insulating) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L5 | 2379 | gate adj dielectric with high-k | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L6 | 175 | dummy adj gate with (periphery peripheral surround surrounding). detx. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/05/02 10:52 |
| L7 | 57 | "4873664" and (dummy inoperable) with (electrode capacitor transistor) and (ferroelectric or dielectric) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |

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| L8 | 9420 | (MATSUDA-A\$ or NAGANO-Y\$ OR UEMOTO-Y\$ OR FUJII-E\$).IN. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L9 | 3 | L8 and (dummy inoperable) with transistor not (ferroelectric or dielectric) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L10 | 9 | feram and dram and ferroelectric.dctx. and @pd<"19971211" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L11 | 8 | ("5281555" "5300814" "5300816" "5689126" "5777358" "5895963" "5913150" "5943591").PN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2008/05/02 10:52 |
| L12 | 1 | (US-5361234-\$).did. | USPAT | OR | OFF | 2008/05/02 10:52 |
| L13 | 4 | L8 and (dummy inoperable) with transistor and (ferroelectric or dielectric) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L14 | 7 | L13 or L9 | US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L15 | 7 | ("4902646" "5225704" "5278105" "5281555" "5410161" "5441915" "5441916").PN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2008/05/02 10:52 |
| L16 | 296 | dummy adj gate with (periphery peripheral surround surrounding) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/05/02 10:52 |
| L17 | 1 | L12 and boundary adj area with dummy.dctx. | USPAT | OR | OFF | 2008/05/02 10:52 |
| L18 | 7165 | (257/295,213,296, E21.664,E27.104).CCLS. | US-PGPUB; USPAT; USOCR | OR | OFF | 2008/05/02 10:52 |

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| L19 | 442 | L18 and dummy | US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L20 | 82 | L19 and @ad<"19971224" | US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L21 | 33 | L20 not dummy adj (cell word adj line) | US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L22 | 4 | L15 and dummy with gate | US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L23 | 731 | gate adj (insulator insulating) near3 (ferroelectric or high-k sbt pzt) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L24 | 10 | ("5959878" "5281555" "5430671") and dummy and array | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L25 | 2 | ("5361224" "5426315"). PN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2008/05/02 10:52 |
| L26 | 7 | sram and gate adj (oxide dielectric insulator insulating) near3 ferroelectric and @pd<"19971211" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/05/02 10:52 |
| L27 | 64 | L18 and dummy adj gate | US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L28 | 6 | sram and gate adj (oxide dielectric insulator insulating) near3 ferroelectric and @pd<"19971211" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |

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| L29 | 6 | "6320214" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L30 | 5189 | feram dram and ferroelectric and @pd<"19971211" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L31 | 180 | (feram or dram and ferroelectric).detx. and @pd<"19971211" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L32 | 43 | L8 and (dummy inoperable) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L33 | 4 | JP-09321248-\$ or JP- 11251554-\$ | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L34 | 15 | (US-6320214-\$ or US- 5946563-\$ or US- 5689456-\$ or US- 5913150-\$ or US- 6150689-\$ or US- 5694353-\$ or US- 5959878-\$ or US- 5396100-\$ or US- 6018215-\$ or US- 5689126-\$ or US- 6091097-\$ or US- 5430671-\$ or US- 5281555-\$ or US- 5361224-\$).did. or (JP- 57180182-\$).did. | USPAT; JPO | OR | OFF | 2008/05/02 10:52 |
| L35 | 5 | (dish dishing) with dummy with capacitor | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/05/02 10:52 |

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| L36 | 76 | L31 and (pzt bto sbt strontium near barium near3 (taltalate titanate)). detx. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L37 | 32 | ("5959878" "5281555" "5430671") and dummy | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L38 | 5 | L11 and gate.detx. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L39 | 5 | L6 and @ad<"19971211" and dummy | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L40 | 141 | L31 and (capacitor pzt bto sbt strontium near barium near3 (taltalate titanate)). detx. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/05/02 10:52 |
| L41 | 28 | ("5959878" "5281555" "5430671") and dummy. detx. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L42 | 105 | dummy with capacitor with layers and (dummy dummies capacitors cell cells wordline wordlines). detx. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L43 | 2 | ((("5,396,100") or ("5,913,150")).PN. | US-PGPUB; USPAT | OR | OFF | 2008/05/02 10:52 |
| L44 | 11 | feram and dram and ferroelectric and @pd<"19971211" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |

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| L45 | 76 | L31 and capacitor.detx. and (pzt bto sbt strontium near barium near3 (taltalate titanate)).detx. | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/05/02 10:52 |
| L46 | 138 | gate adj (insulator insulating oxide dielectric) with ferroelectric and @pd<"19971211" | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2008/05/02 10:52 |
| L47 | 139 | L1 and (ferroelectric perovskite) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/05/02 10:52 |
| L48 | 65 | L47 and (dram 1T near3 1C) | US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/05/02 10:52 |

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